



Future Normal in Semiconductor

2025년 2월 14일(금), 15:10-17:10

Room A(그랜드볼룸 I), 4층

K. Memory (Design & Process Technology) 분과

067_[FA3-K] Material, Process, Structures, Modeling for Advanced Memory Applications

좌장: 박하민 교수(광운대학교), 전종욱 교수(성균관대학교)

<p>초청 FA3-K-1 15:10-15:40</p>	<p>Flexible Synaptic Memristors for Wearable Neuro-Inspired Applications Sin-Hyung Lee^{1,2} ¹School of Advanced Fusion Studies, University of Seoul, ²Department of Intelligent Semiconductor Engineering, University of Seoul</p>
<p>FA3-K-2 15:40-15:55</p>	<p>Wafer Bonding Process와 수율 향상을 위한 계측 김해리, 최별, 안채영, 한경식, 김연수 R&D, SK Hynix</p>
<p>FA3-K-3 15:55-16:10</p>	<p>Enhanced Resistive Switching Stability In a Memristor Array Utilizing Highly Polycrystalline Two-dimensional material Jihoon Yang^{1,2} Aram Yoon^{1,2,3}, Donghyun Lee^{1,2}, IL-John Jung^{1,2}, Dong-Hyeok Lim^{1,2}, Hongsik Jeong^{1,2}, Zonghoon Lee^{1,2,3}, and Soon-Yong Kwon^{1,2} ¹Department of Materials Science and Engineering, UNIST, ²Graduate School of Semiconductor Materials and Devices Engineering, UNIST, ³CMCM, IBS</p>
<p>FA3-K-4 16:10-16:25</p>	<p>Engineering Thermal Diffusion Control in Phase Change Heterostructures for High-Performance, High-Density Phase Change Memory Jun Young Choi¹, Dong Hyun Kim² Jin Suk Oh², Jong Min Joo², Min Su Kang², Ji Eun Park², and Tae Geun Kim^{1,2} ¹Department of Semiconductor System Engineering, Korea University, ²School of Electrical Engineering, Korea University</p>
<p>FA3-K-5 16:25-16:40</p>	<p>Sub 1% of Variance in Two-Dimensional Memristor with Confined Active Electrode Sihoon Son¹, Hyunho Seok¹, Hyunbin Choi², Jinhyoung Lee³, and Taesung Kim^{1,2,3} ¹SKKU Advance Institute of Nano Technology, Sungkyunkwan University, ²Department of Semiconductor Convergence Engineering, Sungkyunkwan University, ³Department of Mechanical Engineering, Sungkyunkwan University</p>



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<p>FA3-K-6 16:40-16:55</p>	<p>Contact Area Size-Dependent Schottky Barrier Height of Memory Device Yoojin Seol, Hyeongyu Kim, Haecheol Hwang, Hyogyung Kim, and Kihyun Kim Department of Electronics and Information Engineering, Jeonbuk National University</p>
<p>FA3-K-7 16:55-17:10</p>	<p>Fully-Coupled Simulation of Bipolar Filamentary Resistive Switching by Phase-field and Electrothermal Models Jinwoo Oh, Dongmyung Jung, and Yongwoo Kwon Department of Materials Science and Engineering, Hongik University</p>